

# IRLR024NTRLPBF Datasheet



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	IRLR024NTRLPBF-DG
Manufacturer	<a href="#">Infineon Technologies</a>
Manufacturer Product Number	IRLR024NTRLPBF
Description	MOSFET N-CH 55V 17A DPAK
Detailed Description	N-Channel 55 V 17A (Tc) 45W (Tc) Surface Mount TO-252AA (DPAK)



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DiGi is a global authorized distributor of electronic components.

## Purchase and inquiry

Manufacturer Product Number:

IRLR024NTRLPBF

Series:

HEXFET®

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

55 V

Drive Voltage (Max Rds On, Min Rds On):

4V, 10V

Vgs(th) (Max) @ Id:

2V @ 250µA

Vgs (Max):

±16V

FET Feature:

-

Operating Temperature:

-55°C ~ 175°C (Tj)

Supplier Device Package:

TO-252AA (DPAK)

Base Product Number:

IRLR024

Manufacturer:

Infineon Technologies

Product Status:

Not For New Designs

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

17A (Tc)

Rds On (Max) @ Id, Vgs:

65mOhm @ 10A, 10V

Gate Charge (Qg) (Max) @ Vgs:

15 nC @ 5 V

Input Capacitance (Ciss) (Max) @ Vds:

480 pF @ 25 V

Power Dissipation (Max):

45W (Tc)

Mounting Type:

Surface Mount

Package / Case:

TO-252-3, DPAK (2 Leads + Tab), SC-63

## Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

International  
**IR** Rectifier

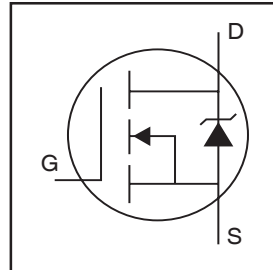
PD- 95081A

IRLR024NPbF

IRLU024NPbF

HEXFET® Power MOSFET

- Logic-Level Gate Drive
- Surface Mount (IRLR024N)
- Straight Lead (IRLU024N)
- Advanced Process Technology
- Fast Switching
- Fully Avalanche Rated
- Lead-Free



$$V_{DSS} = 55V$$

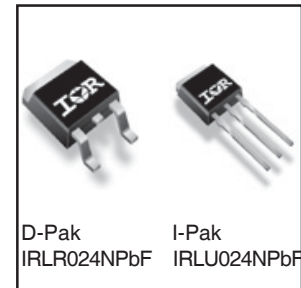
$$R_{DS(on)} = 0.065\Omega$$

$$I_D = 17A$$

### Description

Fifth Generation HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient device for use in a wide variety of applications.

The D-PAK is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 watts are possible in typical surface mount applications.



D-Pak IRLR024NPbF      I-Pak IRLU024NPbF

### Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	17	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	12	
$I_{DM}$	Pulsed Drain Current ①	72	
$P_D @ T_C = 25^\circ C$	Power Dissipation	45	W
	Linear Derating Factor	0.3	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 16$	V
$E_{AS}$	Single Pulse Avalanche Energy ②	68	mJ
$I_{AR}$	Avalanche Current ③	11	A
$E_{AR}$	Repetitive Avalanche Energy ④	4.5	mJ
dv/dt	Peak Diode Recovery dv/dt ⑤	5.0	V/ns
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	

### Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	3.3	°C/W
$R_{\theta JA}$	Case-to-Ambient (PCB mount)**	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	110	

\*\* When mounted on 1" square PCB (FR-4 or G-10 Material) .

For recommended footprint and soldering techniques refer to application note #AN-994

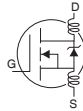
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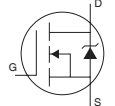
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## IRLR/U024NPbF

International  
IR RectifierElectrical Characteristics @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	—	—	V	$V_{GS} = 0V, I_D = 250\mu\text{A}$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.061	—	V/°C	Reference to $25^\circ\text{C}$ , $I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.065	$\Omega$	$V_{GS} = 10V, I_D = 10A$ ④
		—	—	0.080		$V_{GS} = 5.0V, I_D = 10A$ ④
		—	—	0.110		$V_{GS} = 4.0V, I_D = 9.0A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	2.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
$g_{fs}$	Forward Transconductance	8.3	—	—	S	$V_{DS} = 25V, I_D = 11A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	25	$\mu\text{A}$	$V_{DS} = 55V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 44V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -16V$
$Q_g$	Total Gate Charge	—	—	15	nC	$I_D = 11A$
$Q_{gs}$	Gate-to-Source Charge	—	—	3.7		$V_{DS} = 44V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	—	8.5		$V_{GS} = 5.0V$ , See Fig. 6 and 13 ④ ⑥
$t_{d(on)}$	Turn-On Delay Time	—	7.1	—	ns	$V_{DD} = 28V$
$t_r$	Rise Time	—	74	—		$I_D = 11A$
$t_{d(off)}$	Turn-Off Delay Time	—	20	—		$R_G = 12\Omega, V_{GS} = 5.0V$
$t_f$	Fall Time	—	29	—		$R_D = 2.4\Omega$ , See Fig. 10 ④ ⑥
$L_D$	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
$L_S$	Internal Source Inductance	—	7.5	—		
$C_{iss}$	Input Capacitance	—	480	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	130	—		$V_{DS} = 25V$
$C_{rss}$	Reverse Transfer Capacitance	—	61	—		$f = 1.0\text{MHz}$ , See Fig. 5 ⑥

## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	17	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	72		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 11A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	60	90	ns	$T_J = 25^\circ\text{C}, I_F = 11A$
$Q_{rr}$	Reverse Recovery Charge	—	130	200	nC	$di/dt = 100A/\mu\text{s}$ ④
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$ )				

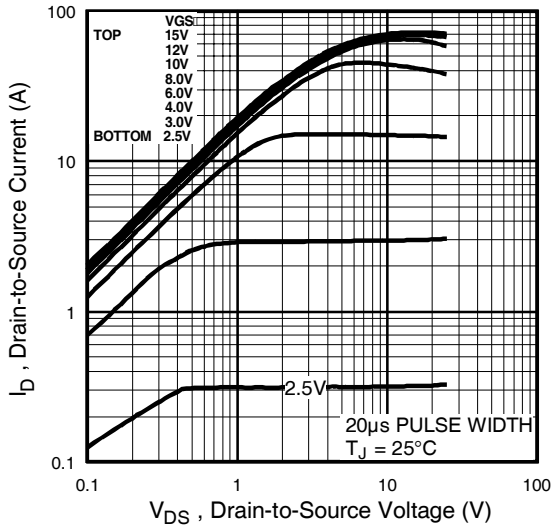
## Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ②  $V_{DD} = 25V$ , starting  $T_J = 25^\circ\text{C}$ ,  $L = 790\mu\text{H}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 11A$ . (See Figure 12)
- ③  $I_{SD} \leq 11A$ ,  $di/dt \leq 290A/\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  
 $T_J \leq 175^\circ\text{C}$

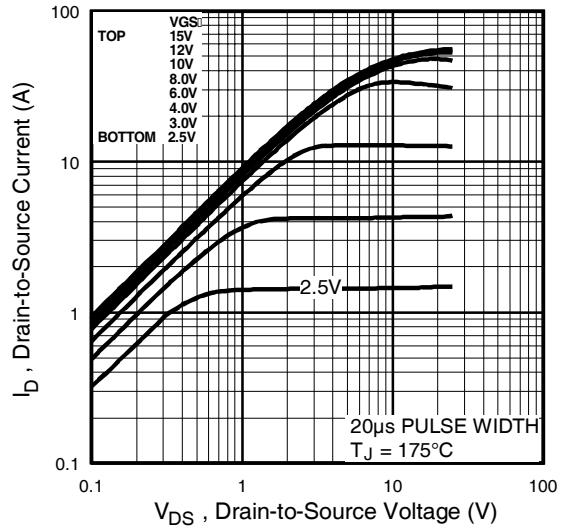
④ Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .⑤ This is applied for I-PAK,  $L_S$  of D-PAK is measured between lead and center of die contact

⑥ Uses IRLZ24N data and test conditions.

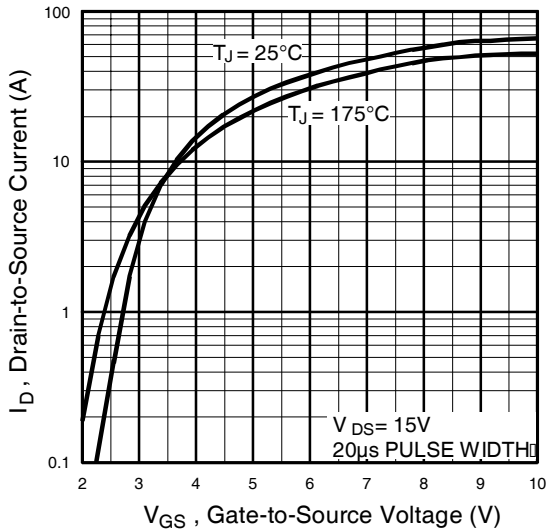
# IRLR/U024NPbF



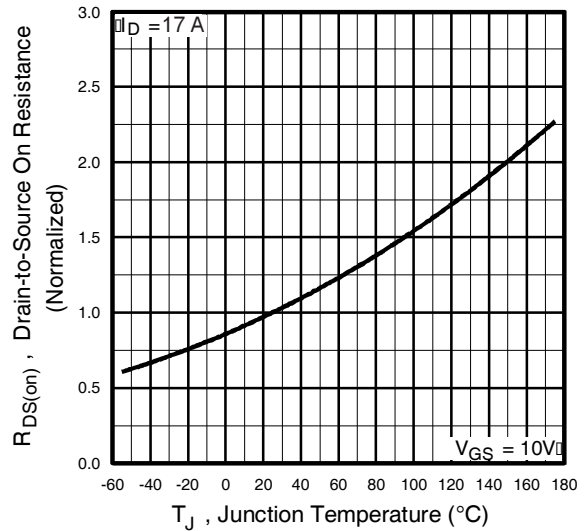
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics

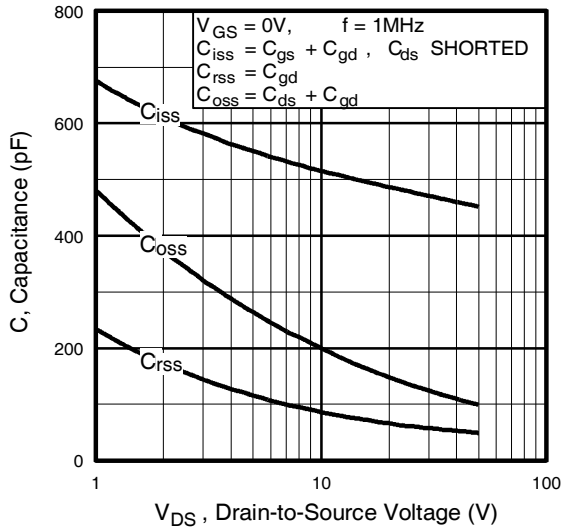


**Fig 3.** Typical Transfer Characteristics

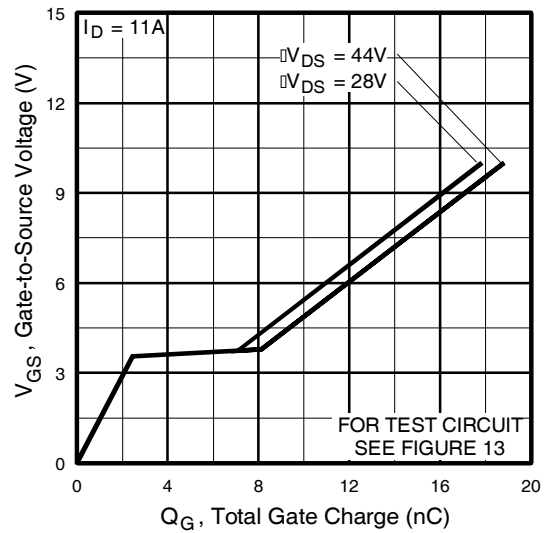


**Fig 4.** Normalized On-Resistance Vs. Temperature

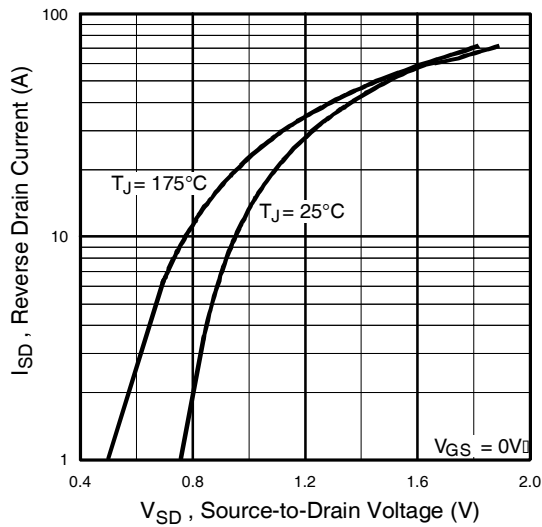
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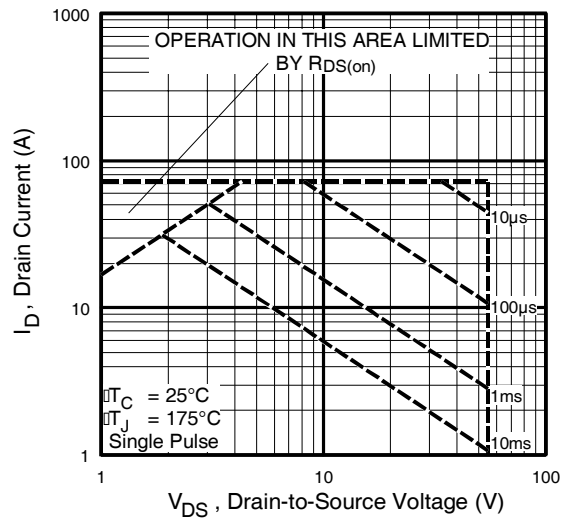
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



**Fig 7.** Typical Source-Drain Diode Forward Voltage



**Fig 8.** Maximum Safe Operating Area

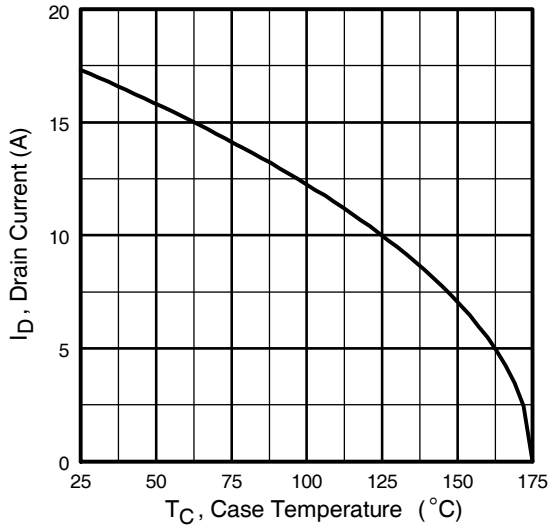


Fig 9. Maximum Drain Current Vs. Case Temperature

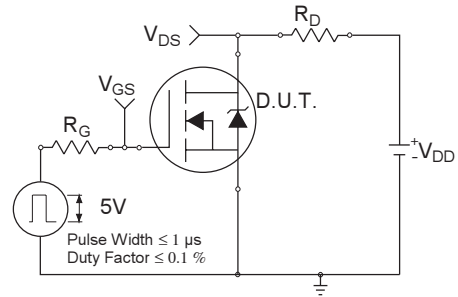


Fig 10a. Switching Time Test Circuit

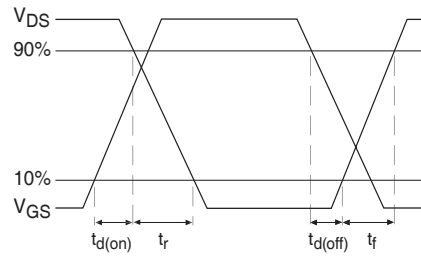


Fig 10b. Switching Time Waveforms

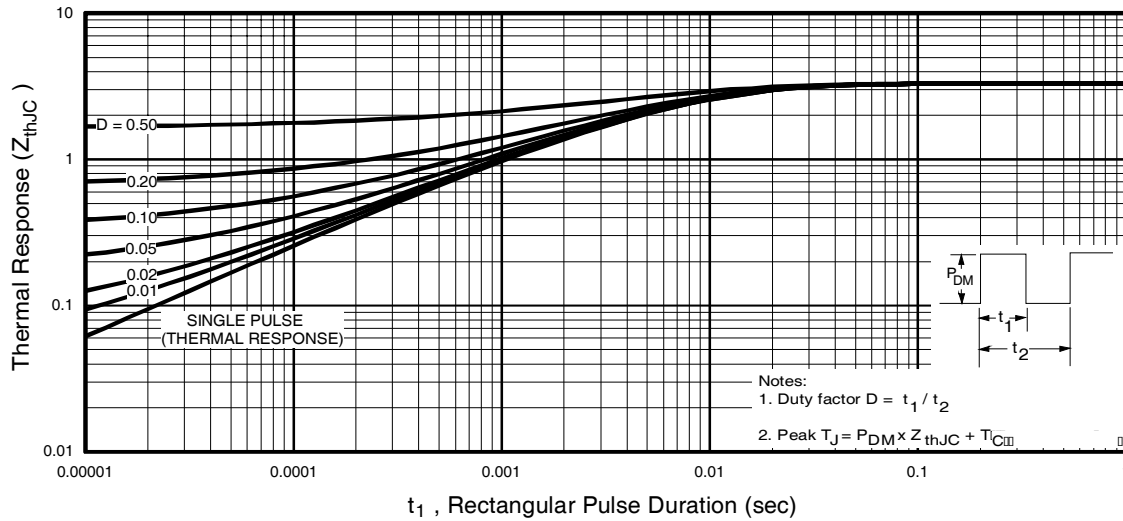
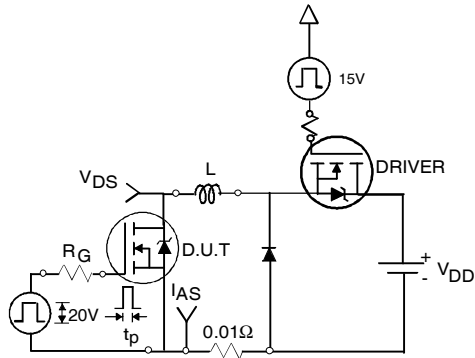


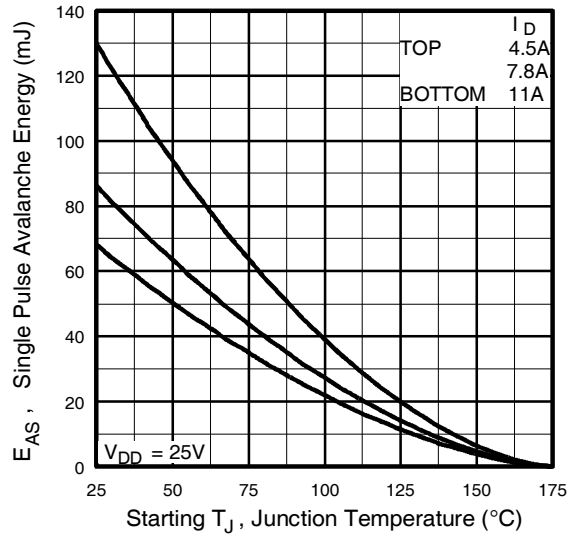
Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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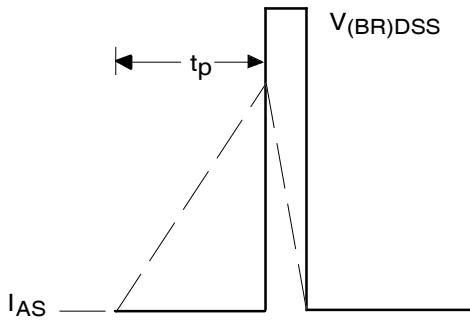
International  
**IRF** Rectifier



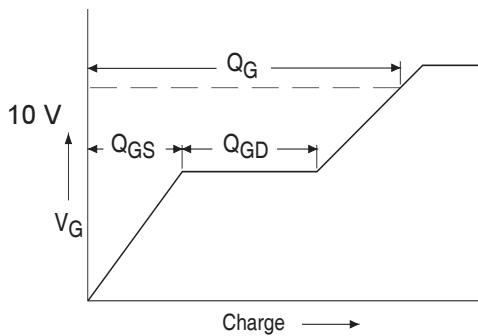
**Fig 12a.** Unclamped Inductive Test Circuit



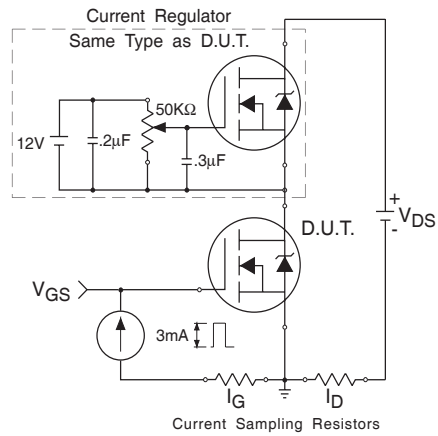
**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



**Fig 12b.** Unclamped Inductive Waveforms



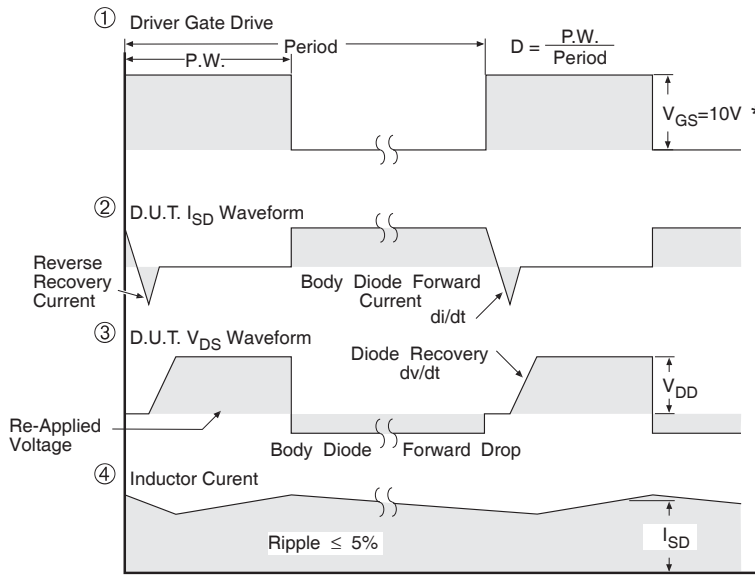
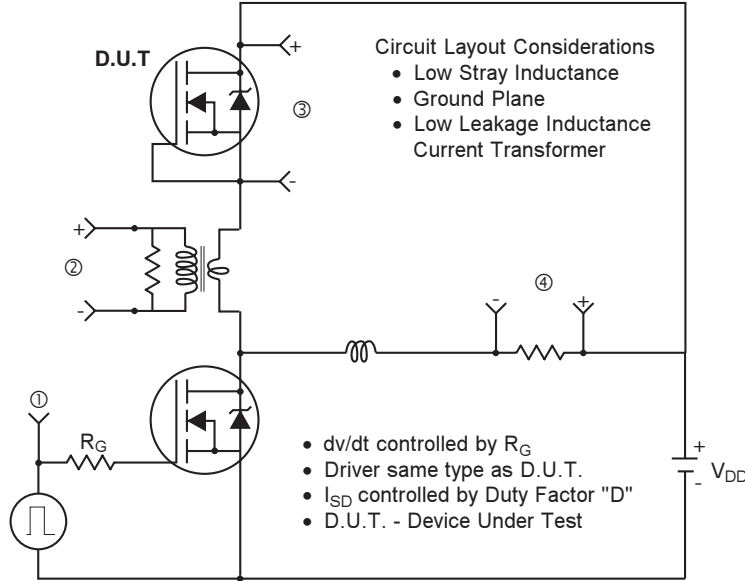
**Fig 13a.** Basic Gate Charge Waveform



**Fig 13b.** Gate Charge Test Circuit



**Peak Diode Recovery dv/dt Test Circuit**



\*  $V_{GS} = 5V$  for Logic Level Devices

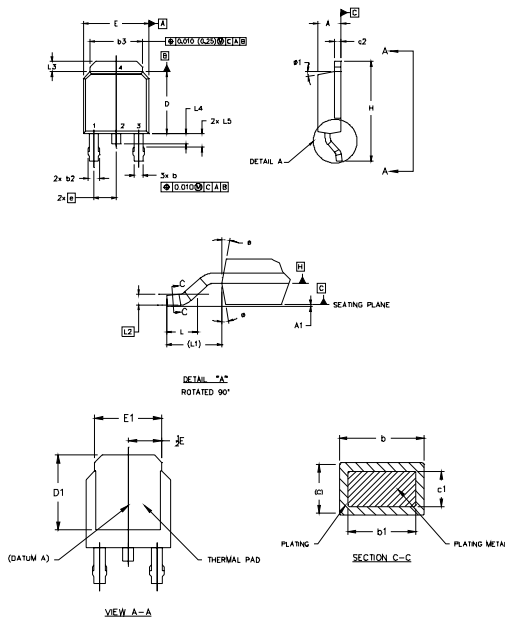
**Fig 14.** For N-Channel HEXFET® MOSFETs

# IRLR/U024NPbF

International  
**IR** Rectifier

## D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

- 1.0 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2.0 DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
- 3.0 LEAD DIMENSION UNCONTROLLED IN L5.
- 4.0 DIMENSION D1 AND E1 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
- 5.0 SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .000 [0.127] AND .010 [0.254] FROM THE LEAD TIP.
- 6.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 7.0 OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1		0.15		.006	
B	0.84	0.89	.033	.035	5
B1	0.84	0.79	.033	0.031	5
B2	0.78	1.54	.031	.061	
B3	0.95	0.46	.038	.018	
C	0.46	0.61	.018	.024	5
C1	0.41	0.56	.016	.022	5
C2	0.46	0.59	.018	.023	5
D	1.91	0.22	.075	.009	6
D1	5.21	-	.205	-	4
E	6.26	6.13	.246	.245	6
E1	4.52	-	.178	-	4
F		2.39		.094	REF
H	0.49	0.41	.019	.016	
L	1.62	1.76	.064	.070	
L1		2.74		.108	REF
L2		0.50		.020	REF
L3		0.89		.035	
L4		0.89		.035	
L5		1.14		.045	
L6		0"		0"	
L7		0"		0"	
L8		0"		0"	
L9		0"		0"	
L10		0"		0"	
L11		0"		0"	
L12		0"		0"	
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L98		0"		0"	
L99		0"		0"	
L100		0"		0"	

LEAD ASSIGNMENTS

- 1- GATE
- 2- DRAIN
- 3- SOURCE
- 4- DRAIN

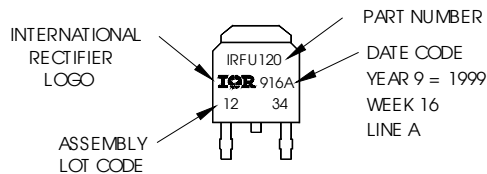
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- 1- GATE
- 2- COLLECTOR
- 3- EMITTER
- 4- COLLECTOR

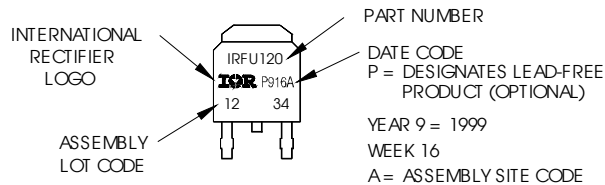
## D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120  
WITH ASSEMBLY  
LOT CODE 1234  
ASSEMBLED ON WW 16, 1999  
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position  
indicates "Lead-Free"

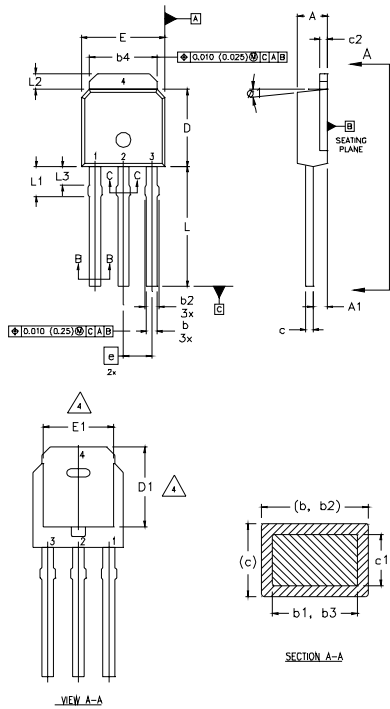


OR



### I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
  - 2 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
  - 3 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
  - 4 THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
  - 5 LEAD DIMENSION UNCONTROLLED IN L3.
  - 6 DIMENSION b1, b3 APPLY TO BASE METAL ONLY.
  - 7 OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA.
  - 8 CONTROLLING DIMENSION : INCHES.

LEAD ASSIGNMENTS

HEXFEE

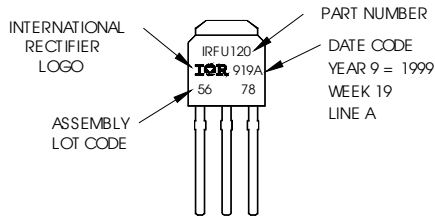
- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	0.086	.094	
A1	0.89	1.14	0.035	0.045	
b	0.64	0.88	0.025	0.035	
b1	0.64	0.79	0.025	0.031	4
b2	0.76	1.14	0.030	0.045	
b3	0.76	1.04	0.030	0.041	
b4	5.00	5.46	0.195	0.215	4
c	0.46	0.61	0.018	0.024	
c1	0.41	0.56	0.016	0.022	
c2	.046	0.86	0.018	0.035	
D	5.97	6.22	0.235	0.245	3, 4
D1	5.21	-	0.205	-	4
E	6.36	6.73	0.250	0.265	3, 4
E1	4.32	-	0.170	-	4
e	2.29		0.090 BSC		
L	8.89	9.60	0.350	0.380	
L1	1.91	2.29	0.075	0.090	
L2	0.89	1.27	0.035	0.050	4
L3	1.14	1.52	0.045	0.060	5
ø1	Ø	15'	Ø	15'	

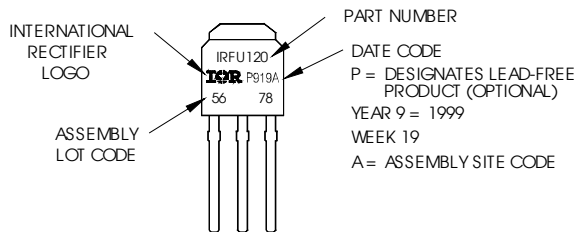
### I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120 WITH ASSEMBLY LOT CODE 5678 ASSEMBLED ON WW 19, 1999 IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position indicates "Lead-Free"



OR

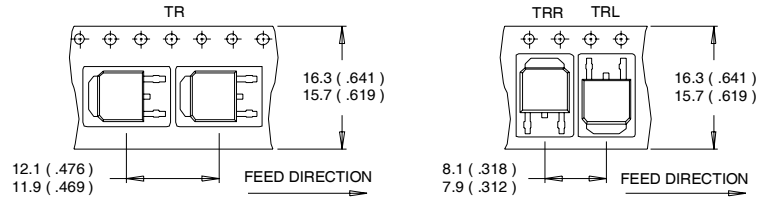


# IRLR/U024NPbF

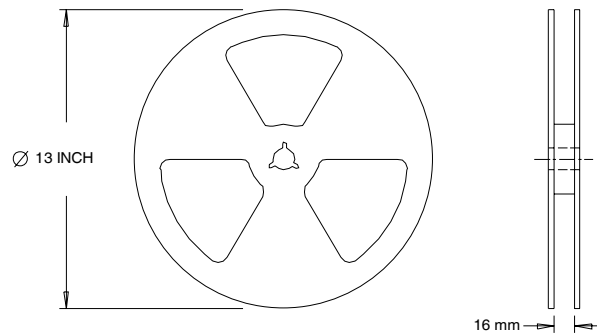


## D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS ( INCHES ).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. OUTLINE CONFORMS TO EIA-481.

Data and specifications subject to change without notice.



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Note: For the most current drawings please refer to the IR website at:  
<http://www.irf.com/package/>

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